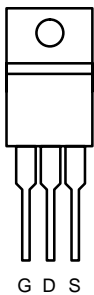




P-Channel Enhancement-Mode Transistors

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A) ^a
-30	0.007 @ $V_{GS} = -10$ V	± 75
	0.010 @ $V_{GS} = -4.5$ V	± 75

TO-220AB

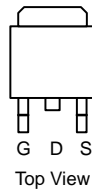


Top View

SUP75P03-07

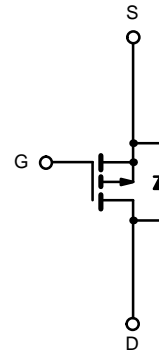
DRAIN connected to TAB

TO-263



Top View

SUB75P03-07



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)			
Parameter	Symbol	Limit	Unit
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_J = 175^\circ\text{C}$)	I_D	$T_C = 25^\circ\text{C}$	-75^a
		$T_C = 125^\circ\text{C}$	-65
Pulsed Drain Current	I_{DM}	-240	A
Avalanche Current	I_{AR}	-60	
Repetitive Avalanche Energy ^b	E_{AR}	L = 0.1 mH	180
Power Dissipation		$T_C = 25^\circ\text{C}$ (TO-220AB and TO-263)	187^d
	$T_A = 25^\circ\text{C}$ (TO-263) ^c	3.75	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 175	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Junction-to-Ambient	R_{thJA}	PCB Mount (TO-263) ^c	40
		Free Air (TO-220AB)	62.5
Junction-to-Case	R_{thJC}	0.8	$^\circ\text{C/W}$

Notes:

- a. Package limited.
- b. Duty cycle $\leq 1\%$.
- c. When mounted on 1" square PCB (FR-4 material).
- d. See SOA curve for voltage derating.



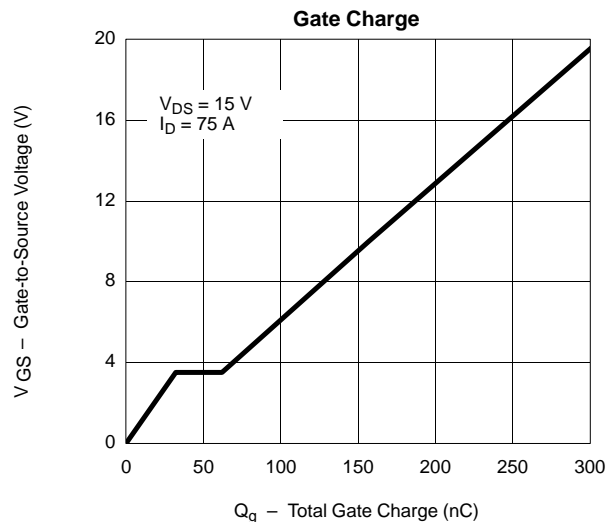
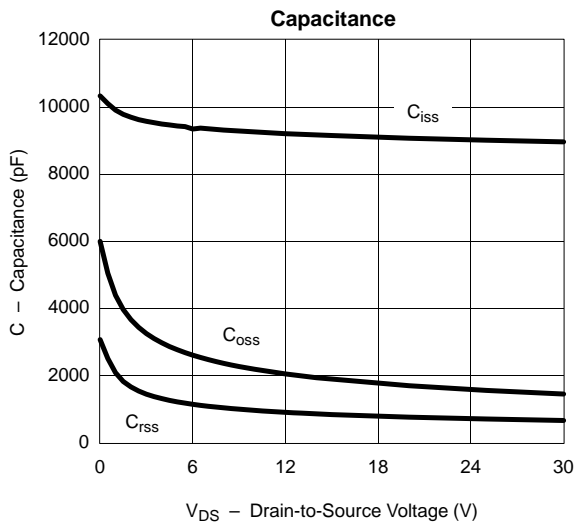
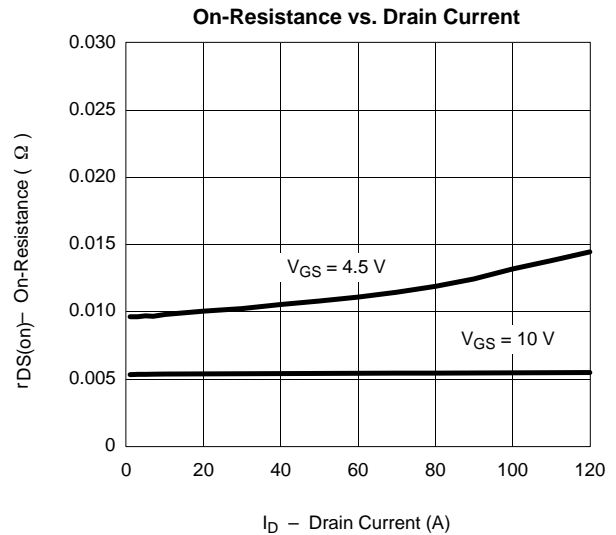
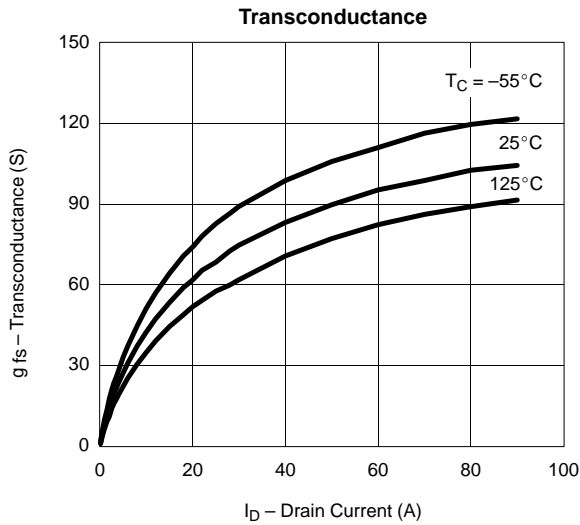
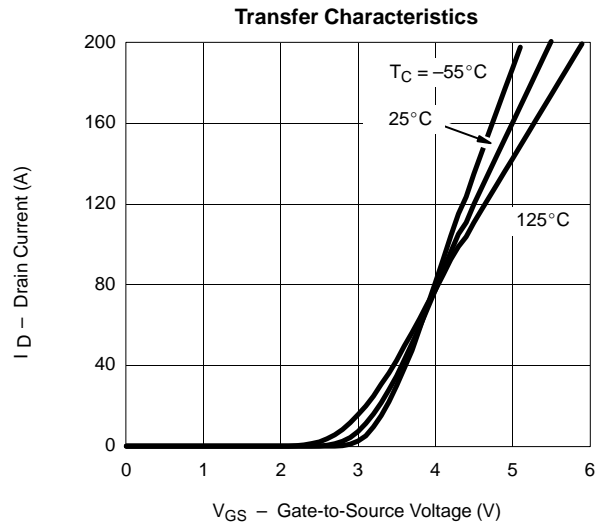
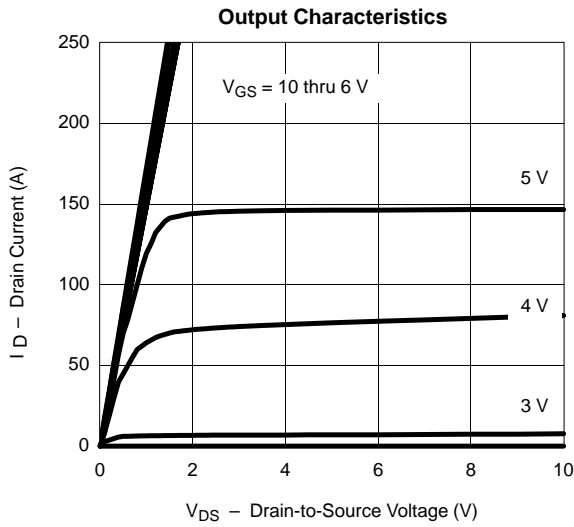
SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = -250 μA	-30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-1		-3	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -30 V, V _{GS} = 0 V			-1	μA
		V _{DS} = -30 V, V _{GS} = 0 V, T _J = 125 °C			-50	
		V _{DS} = -30 V, V _{GS} = 0 V, T _J = 175 °C			-250	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = -5 V, V _{GS} = -10 V	-120			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = -10 V, I _D = -30 A		0.0055	0.007	Ω
		V _{GS} = -10 V, I _D = -30 A, T _J = 125 °C			0.010	
		V _{GS} = -10 V, I _D = -30 A, T _J = 175 °C			0.013	Ω
		V _{GS} = -4.5 V, I _D = -20 A		0.008	0.010	
Forward Transconductance ^a	g _{fs}	V _{DS} = -15 V, I _D = -75 A	20			S
Dynamic^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = -25 V, f = 1 MHz		9000		pF
Output Capacitance	C _{oss}			1565		
Reversen Transfer Capacitance	C _{rss}			715		
Total Gate Charge ^c	Q _g	V _{DS} = -15 V, V _{GS} = -10 V, I _D = -75 A		160	240	nC
Gate-Source Charge ^c	Q _{gs}			32		
Gate-Drain Charge ^c	Q _{gd}			30		
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = -15 V, R _L = 0.2 Ω I _D ≈ -75 A, V _{GEN} = -10 V, R _G = 2.5 Ω		25	40	ns
Rise Time ^c	t _r			225	360	
Turn-Off Delay Time ^c	t _{d(off)}			150	240	
Fall Time ^c	t _f			210	340	
Source-Drain Diode Ratings and Characteristics (T_C = 25 °C)^b						
Continuous Current	I _s				-75	A
Pulsed Current	I _{SM}				-240	
Forward Voltage ^a	V _{SD}	I _F = -75 A, V _{GS} = 0 V		-1.2	-1.5	V
Reverse Recovery Time	t _{rr}	I _F = -75 A, di/dt = 100 A/μs		55	100	ns
Peak Reverse Recovery Current	I _{RM(REC)}			2.5	5	A
Reverse Recovery Charge	Q _{rr}			0.07	0.25	μC

Notes:

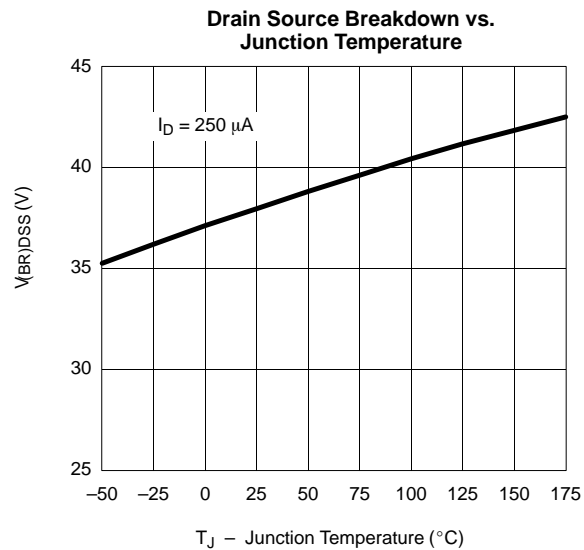
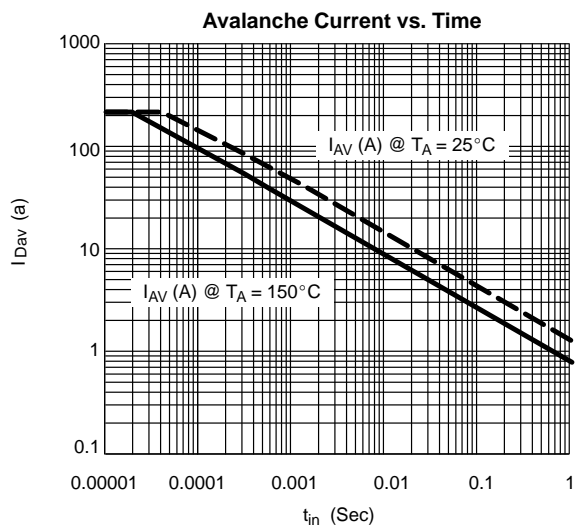
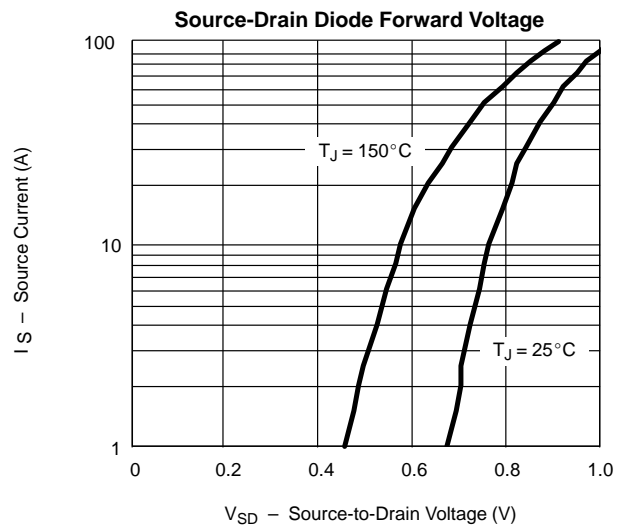
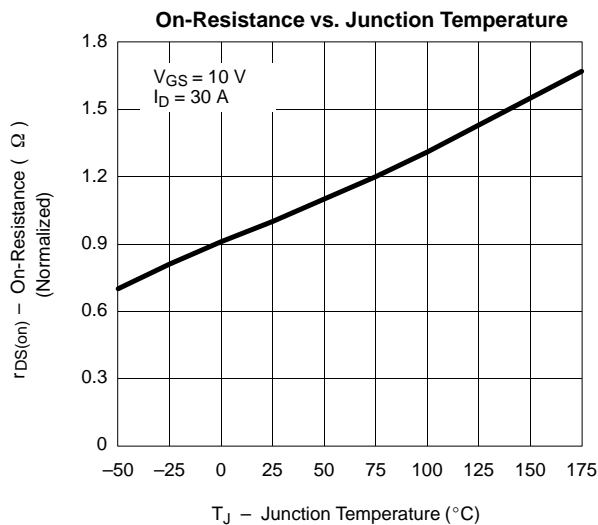
- a. Guaranteed by design, not subject to production testing.
- b. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- c. Independent of operating temperature.



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



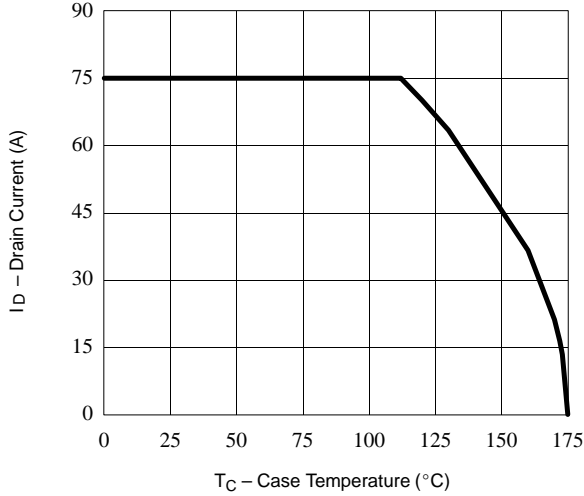
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



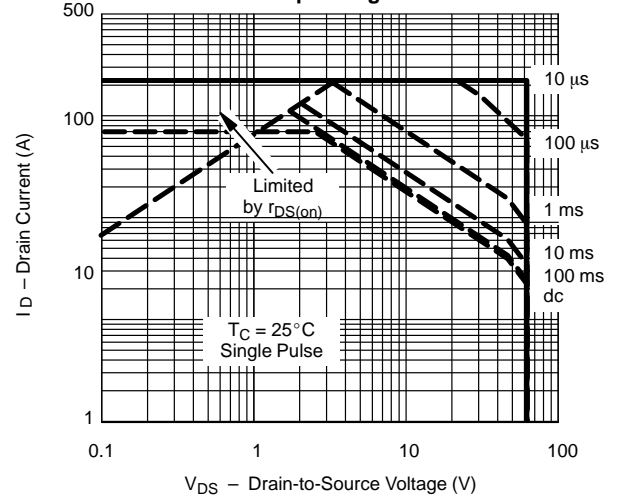


THERMAL RATINGS

Maximum Avalanche and Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

